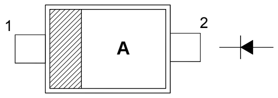
SDS160EWT

SILICON EPITAXIAL PLANAR SWITCHING DIODE

for ultra high speed switching application

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View
Marking Code: "**A**"
Simplified outline SOD-523 and symbol

Features

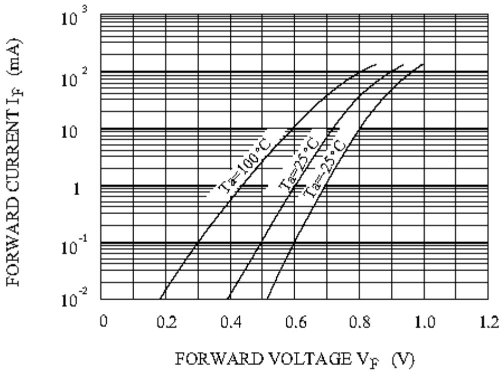
- Fast reverse recovery time
- Small total capacitance
- Low forward voltage

Absolute Maximum Ratings (T_a = 25 °C)

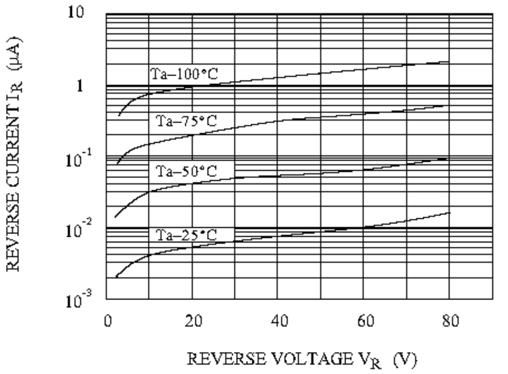
Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	85	V
Reverse Voltage	V_R	80	V
Average Forward Current	I_O	100	mA
Peak Forward Current	I_{FM}	300	mA
Surge Current (10 ms)	I_{FSM}	2	A
Power Dissipation	P_D	150	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

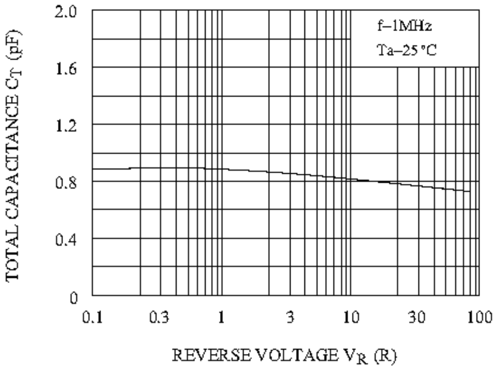
Parameter	Symbol	Max.	Unit
Forward Voltage at I_F = 100 mA	V_F	1.2	V
Reverse Current at V_R = 80 V	I_R	0.5	µA
Total Capacitance at V_R = 0 V, f = 1 MHz	C_T	3	pF
Reverse Recovery Time at I_{rr} = 0.1 X I_R, I_F = I_R = 10 mA, R_L = 100 Ω	t_{rr}	4	ns



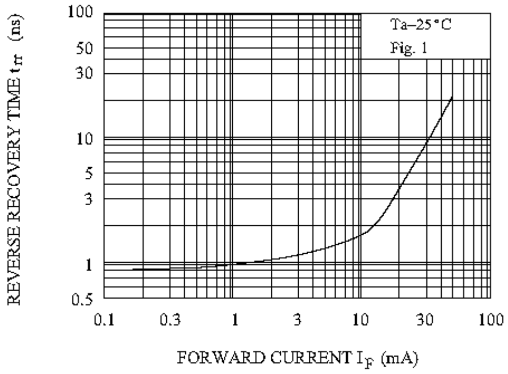
I_F - V_F



I_R - V_R



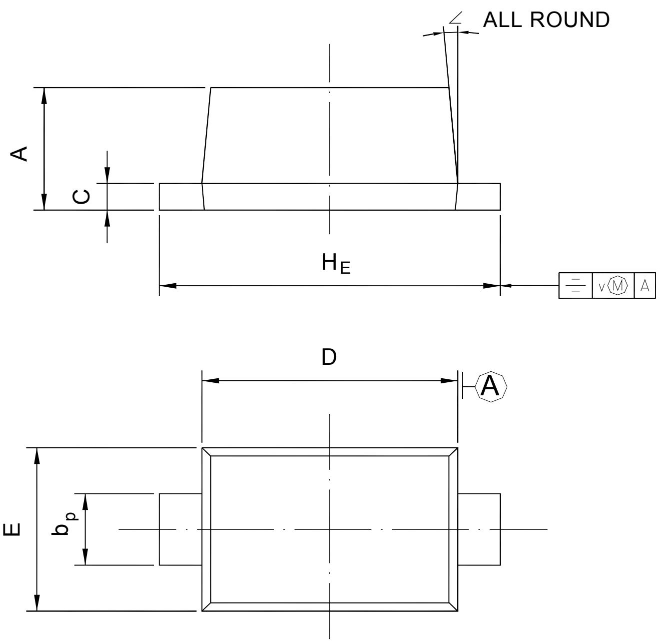
C_T - V_R



t_{rr} - I_F

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-523**



UNIT	A	b_p	C	D	E	H_E	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.127	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°